THIN FILM TRANSISTOR AND USE OF SAME

Cross Reference to Related Applications

This application is a divisional of U.S. Application Serial No. 10/222,339, filed

NOW US PRIME NAMES 6,734,505

August 15, 2002, which claims priority of Japanese Serial No. 2001-256963, filed August

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Background of the Invention

The present invention relates to a thin film transistor including a so-called dual gate structure for driving the thin film transistor by using a plurality of gate electrodes and a method of manufacturing the thin film transistor. The present invention further relates to a display device including the thin film transistor, and a method of driving the display device.

An organic LED (light emitting diode) has a very high response speed and is a self-emitting device, and thus, it is expected that the application of the organic LED to a display device will allow providing an excellent flat display device having a wide viewing angle. The application of the organic LED to the flat display device replaces a liquid crystal display device. The above-mentioned organic LED is a current-driven element and, thus, the achievement of high-resolution display requires a continuous feed of a current through the organic LED element even during non-selection of a scanning line.

FIG. 9 is a diagram showing a circuit configuration for driving an organic LED, which has been heretofore proposed. The conventional circuit configuration shown in

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